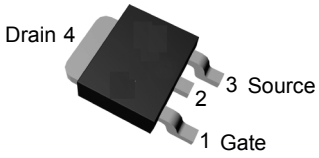
Features

- 20V/85A,
  $R_{DS(ON)}$= 4mΩ (typ.) @ V_{GS}=4.5V
  $R_{DS(ON)}$= 5mΩ (typ.) @ V_{GS}=2.5V
- Reliable and Rugged
- Lead Free and Green Devices Available
  (RoHS Compliant)

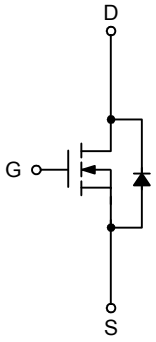
Applications

- Power Motor Controls.
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Industrial.
- Load Switching.

Pin Description



Top View of TO-252



N-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V_{DSS}	Drain-Source Voltage		20	V
V_{GSS}	Gate-Source Voltage		±12	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	T_C=25°C	85	A
I_D	Continuous Drain Current	T_C=25°C	85	A
		T_C=100°C	64	
I_{DM} [a]	Pulse Drain Current Tested	T_C=25°C	255	A
P_D	Maximum Power Dissipation	T_C=25°C	50	W
		T_C=100°C	20	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	t ≤ 10s	20	°C/W
		Steady State	50	
I_{AS} [b]	Avalanche Current, Single pulse	L=0.5mH	19	A
E_{AS} [b]	Avalanche Energy, Single pulse	L=0.5mH	212	mJ

Note a：*Current is limited by bond wire.

Note b：UIS tested and pulse width are limited by maximum junction temperature 150°C (initial temperature T_j=25°C).

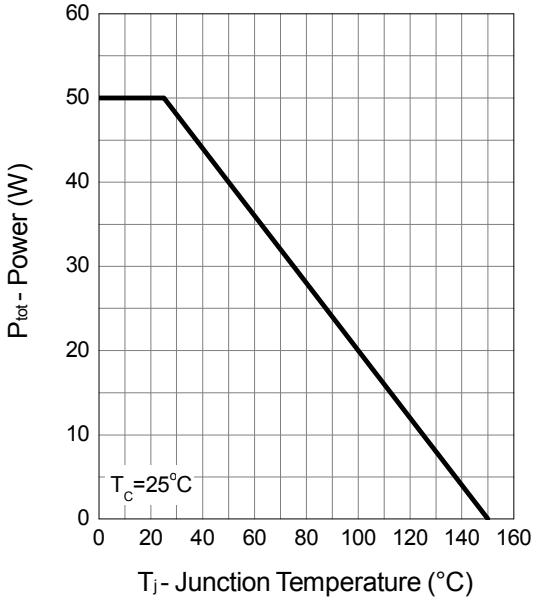
Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V	-	-	1	μA
		T_J=85°C		-	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	0.4	0.75	1	V
I_{GSS}	Gate Leakage Current	V_{GS}=±12V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$ [c]	Drain-Source On-state Resistance	V_{GS}=4.5V, I_{DS}=85A	-	4.0	6	mΩ
		V_{GS}=2.5V, I_{DS}=60A	-	5.0	7.5	
Diode Characteristics						
V_{SD} [c]	Diode Forward Voltage	I_{SD}=10A, V_{GS}=0V	-	0.7	1.1	V
t_{rr}	Reverse Recovery Time	I_{DS}=20A, dI_{SD}/dt=100A/μs	-	16	-	ns
t_a	Charge Time		-	9.2	-	
t_b	Discharge Time		-	7	-	
Q_{rr}	Reverse Recovery Charge		-	7.5	-	nC
Dynamic Characteristics [d]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz	-	2.5	5	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, Frequency=1.0MHz	-	1217	-	pF
C_{oss}	Output Capacitance		-	270	-	
C_{rss}	Reverse Transfer Capacitance		-	190	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=15V, R_L=15Ω, I_{DS}=1A, V_{GEN}=10V, R_G=6Ω	-	13	-	ns
t_r	Turn-on Rise Time		-	11.6	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	85	-	
t_f	Turn-off Fall Time		-	42	-	
Gate Charge Characteristics [d]						
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=4.5V, I_{DS}=25A	-	23	-	nC
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=10V, I_{DS}=25A	-	50	-	
Q_{gth}	Threshold Gate Charge		-	1.25	-	
Q_{gs}	Gate-Source Charge		-	2.8	-	
Q_{gd}	Gate-Drain Charge		-	8.2	-	

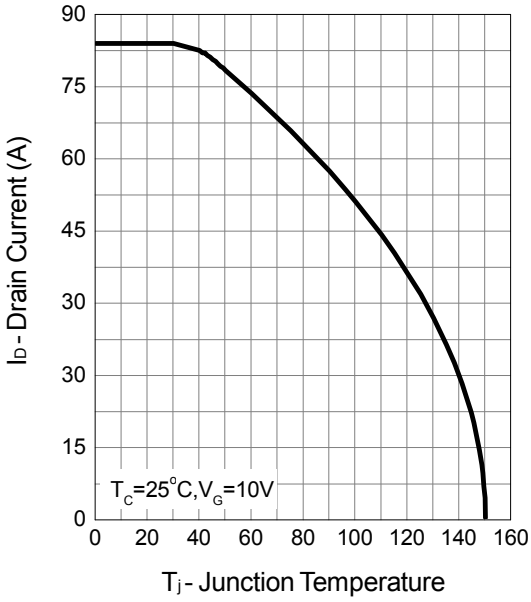
Note c：Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note d：Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

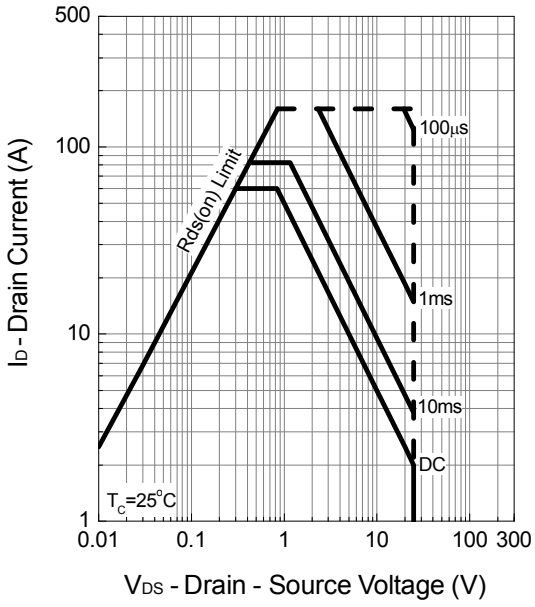
Power Dissipation



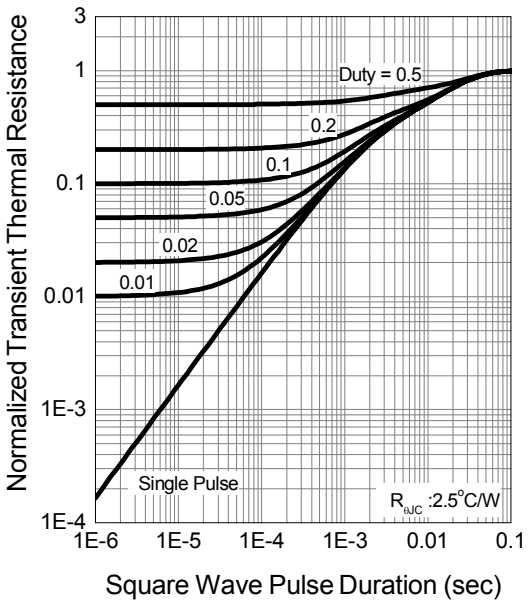
Drain Current



Safe Operation Area

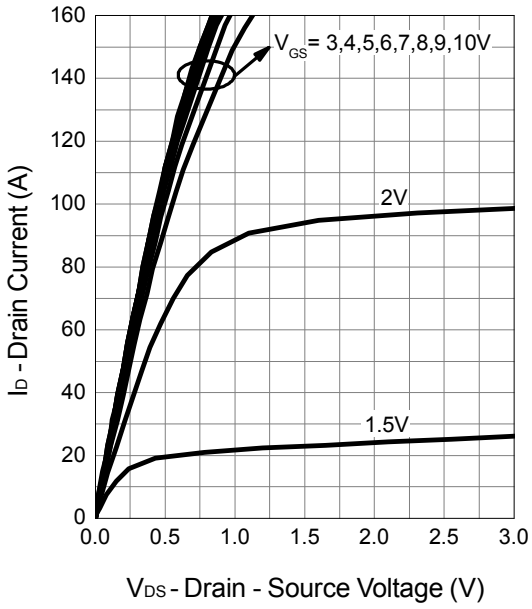


Thermal Transient Impedance

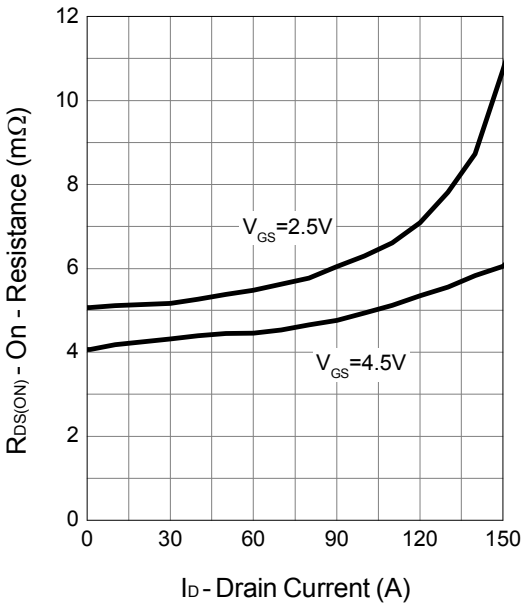


Typical Operating Characteristics (Cont.)

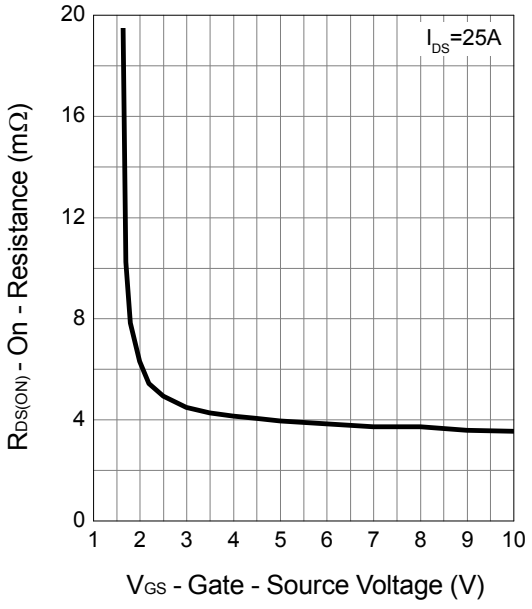
Output Characteristics



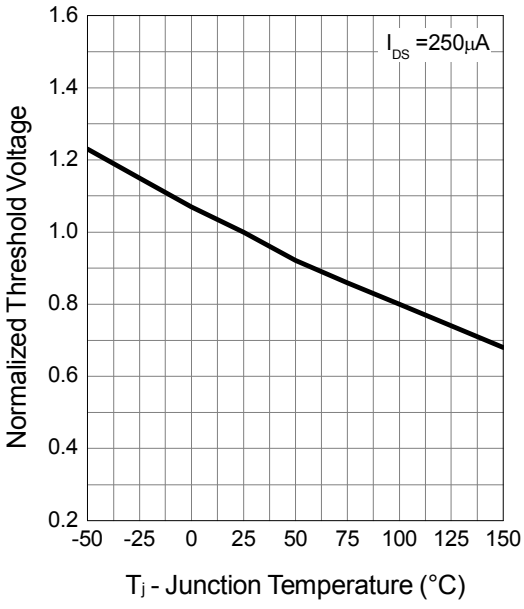
Drain-Source On Resistance



Gate-Source On Resistance

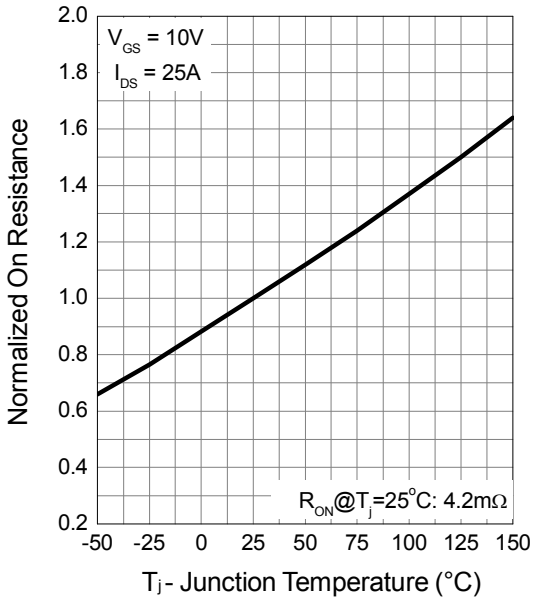


Gate Threshold Voltage

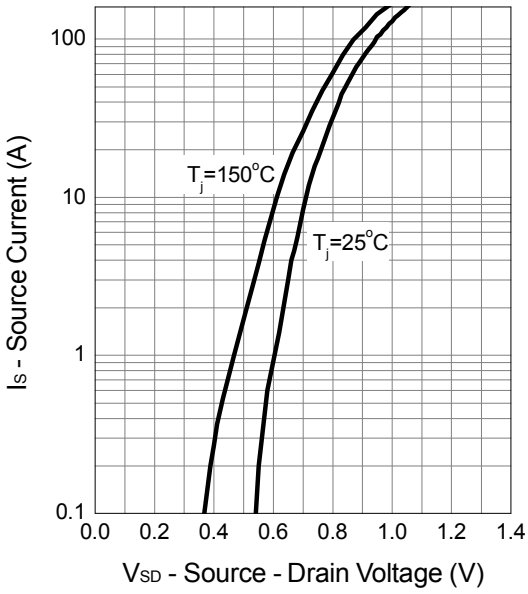


Typical Operating Characteristics (Cont.)

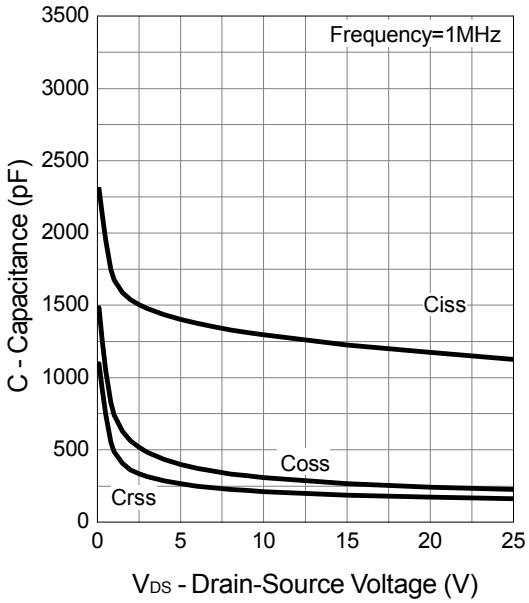
Drain-Source On Resistance



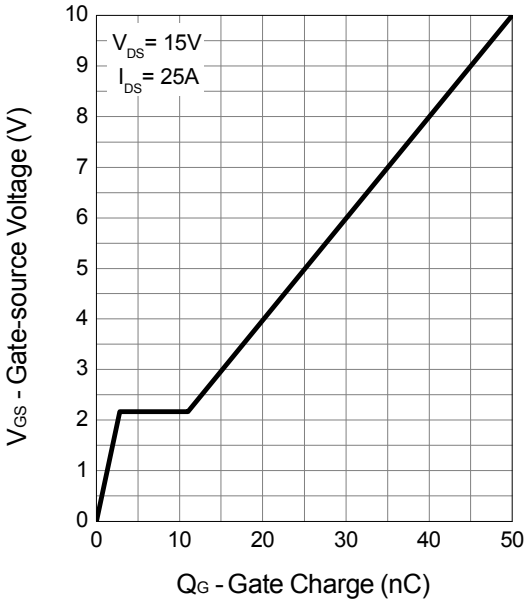
Source-Drain Diode Forward



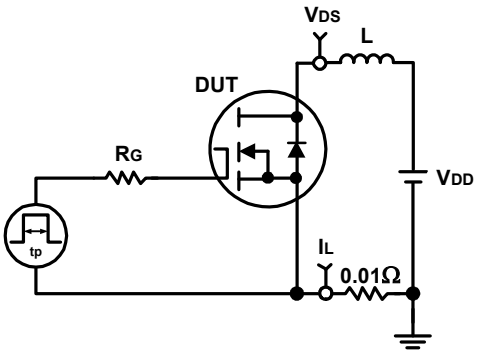
Capacitance

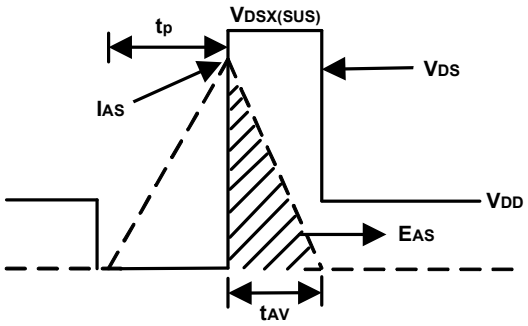


Gate Charge

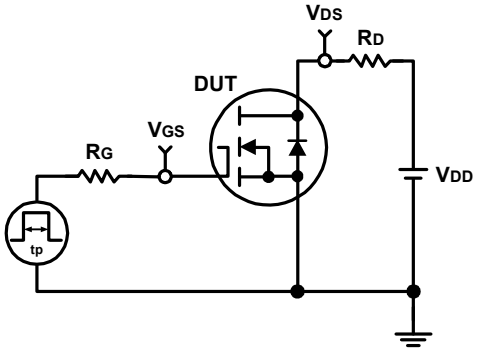


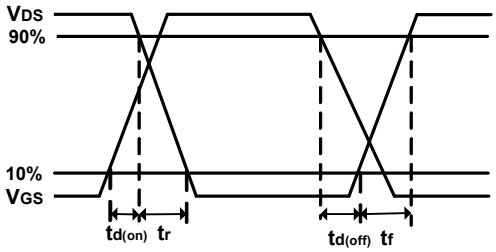
Avalanche Test Circuit and Waveforms



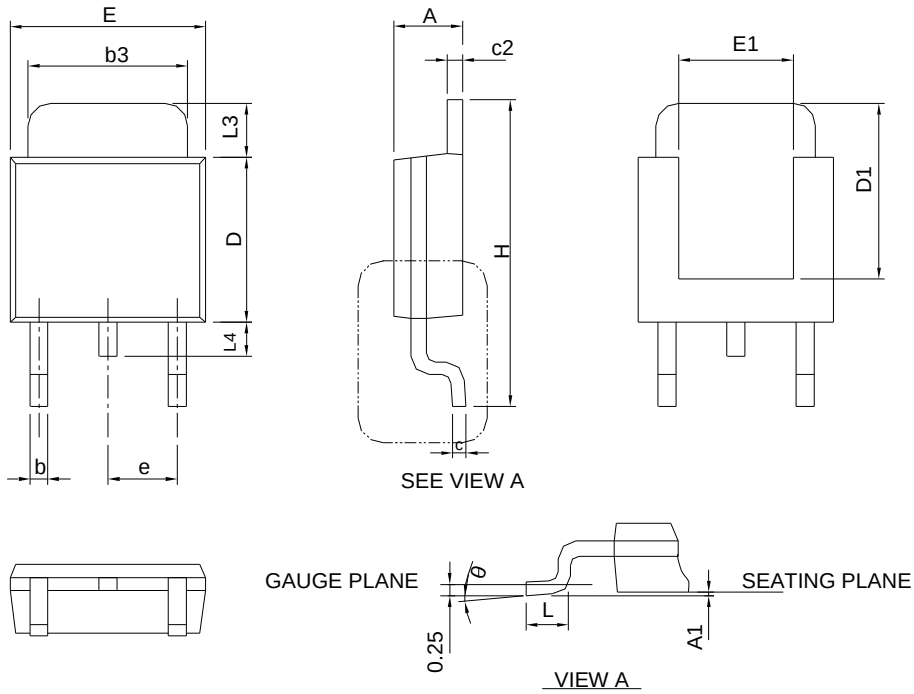


Switching Time Test Circuit and Waveforms





Package Information



SYMBOL	TO-252			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	-	0.13	-	0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4	-	1.02	-	0.040
θ	0°	8°	0°	8°

Note : Follow JEDEC TO-252 .

RECOMMENDED LAND PATTERN